

## SILICON BRIDGE RECTIFIER

VOLTAGE RANGE: 50 --- 1000 V

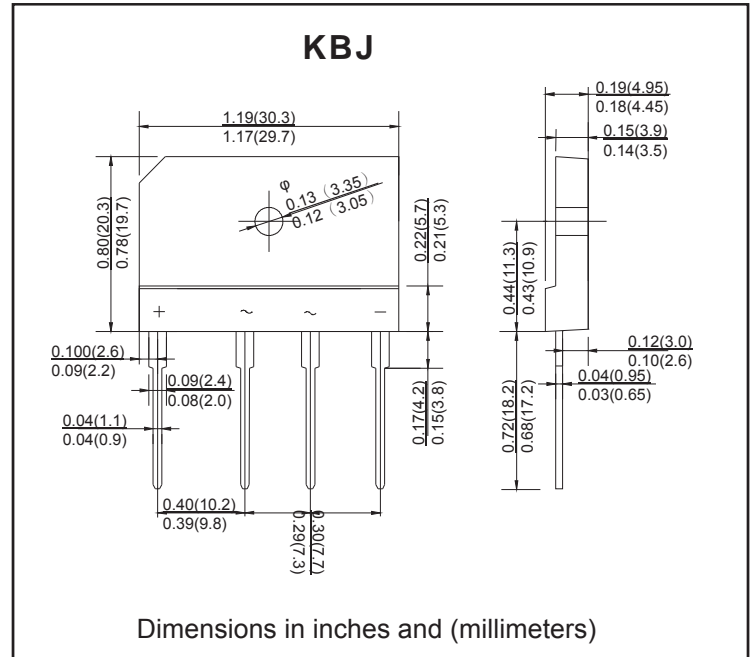
CURRENT: 6.0 A

### FEATURES

- Rating to 1000V PRV
- Surge overload rating to 150 Amperes peak
- Ideal for printed circuit board
- Reliable low cost construction utilizing m olded plastic technique results in inexpensive product
- Lead solderable per MIL-STD-202 m ethod 208
- Glass passivated chip junctions

### MECHANICAL DATA

- Polarity: Sym bols molded on body
- Mounting position: Any



### MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted) Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

		KBJ 6A	KBJ 6B	KBJ 6D	KBJ 6G	KBJ 6J	KBJ 6K	KBJ 6M	UNITS
Maximum recurrent peak reverse voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	$V_{DC}$	50	100	200	400	600	800	1000	V
Maximum average forward Output current @ $T_A=110^\circ\text{C}$	$I_{F(AV)}$	6.0							A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load	$I_{FSM}$	150.0							A
Maximum instantaneous forward voltage at 3.0 A	$V_F$	1.0							V
Maximum reverse current @ $T_A=25^\circ\text{C}$ at rated DC blocking voltage @ $T_A=100^\circ\text{C}$	$I_R$	10.0 1.0							$\mu\text{A}$ mA
Typical junction capacitance per element	$C_J$	55							pF
Typical thermal resistance	$R_{\theta JC}$	1.8							$^\circ\text{C}/\text{W}$
Operating junction temperature range	$T_J$	- 55 --- + 150							$^\circ\text{C}$
Storage temperature range	$T_{STG}$	- 55 --- + 150							$^\circ\text{C}$

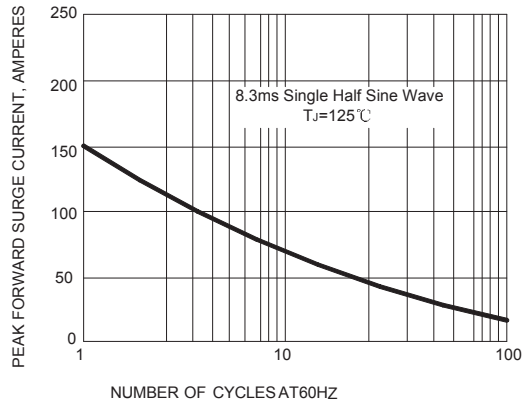
NOTES: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC

2. Device mounted on 300mm X 300mm X 1.6mm cu Plate heatsink.

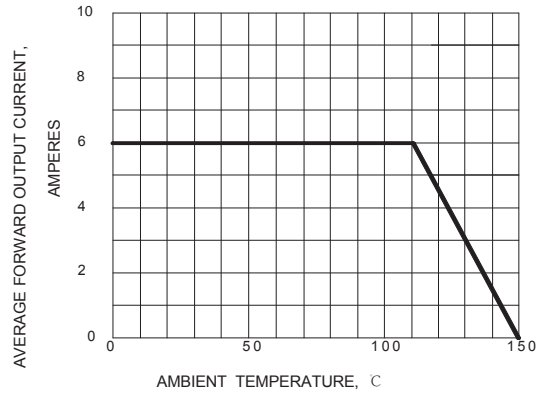


# RATINGS AND CHARACTERISTIC CURVES

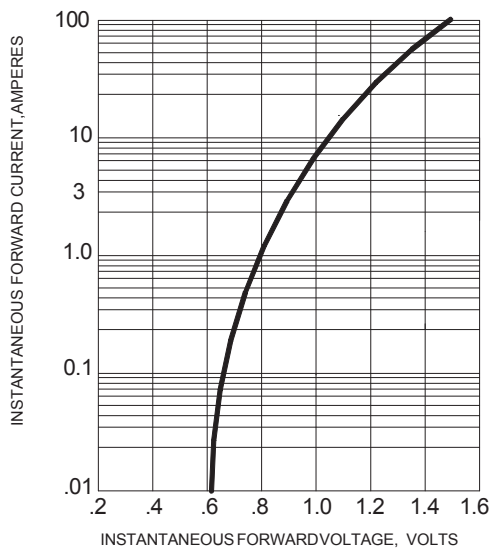
**FIG.1 – PEAK FORWARD SURGE CURRENT**



**FIG.2 – FORWARD DERATING CURVE**



**FIG.3 -- TYPICAL FORWARD CHARACTERISTIC**



**FIG.4 -- TYPICAL JUNCTION CAPACITANCE**

